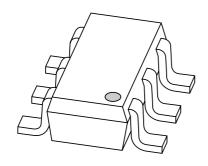
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# BC817DS NPN general purpose double transistor

Product data sheet Supersedes data of 2002 Aug 09 2002 Nov 22



# NPN general purpose double transistor

**BC817DS** 

#### **FEATURES**

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

#### **APPLICATIONS**

- · General purpose switching and amplification
- Push-pull amplifiers
- · Multi-phase stepper motor drivers.

#### **DESCRIPTION**

NPN transistor pair in a SOT457 (SC-74) plastic package.

#### **MARKING**

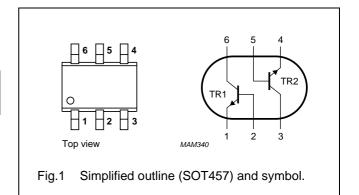
TYPE NUMBER	MARKING CODE
BC817DS	N3

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	45	V
I <sub>C</sub>	collector current (DC)	500	mA
I <sub>CM</sub>	peak collector current	1	Α

#### **PINNING**

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transi	Per transistor unless otherwise specified				
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		_	500	mA
I <sub>CM</sub>	peak collector current		_	1	Α
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	370	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device	9		•		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	600	mW

#### Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	208	K/W

#### Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

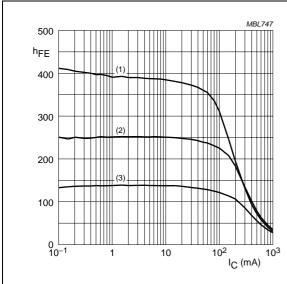
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0	-	_	100	nA
		V <sub>CB</sub> = 20 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	_	_	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 100 mA; note 1	160	-	400	
		V <sub>CE</sub> = 1 V; I <sub>C</sub> = 500 mA; note 1	40	_	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 500 \text{ mA}$ ; $I_B = 50 \text{ mA}$ ; note 1	-	-	700	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = 1 \text{ V; } I_{C} = 500 \text{ mA;}$ notes 1 and 2	_	_	1.2	V
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	5	_	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	100	_	_	MHz

#### Notes

- 1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$
- 2.  $V_{BE}$  decreases by approximately -2 mV/K with increasing temperature.

# NPN general purpose double transistor

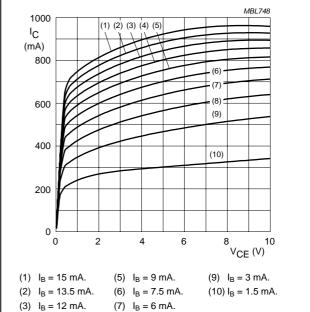
**BC817DS** 



 $V_{CE} = 1 V$ .

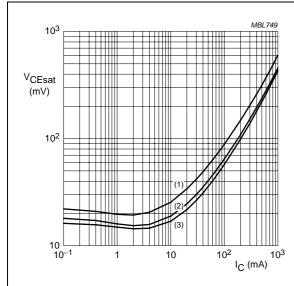
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.2 DC current gain as a function of collector current; typical values.



- (4)  $I_B = 10.5 \text{ mA}.$
- (8)  $I_B = 4.5 \text{ mA}.$

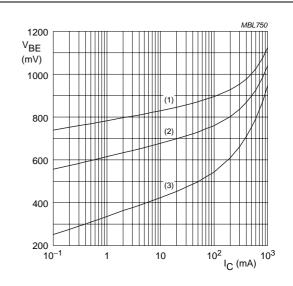
Collector current as a function of collector-emitter voltage; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = 1 V.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter voltage as a function of collector current; typical values.

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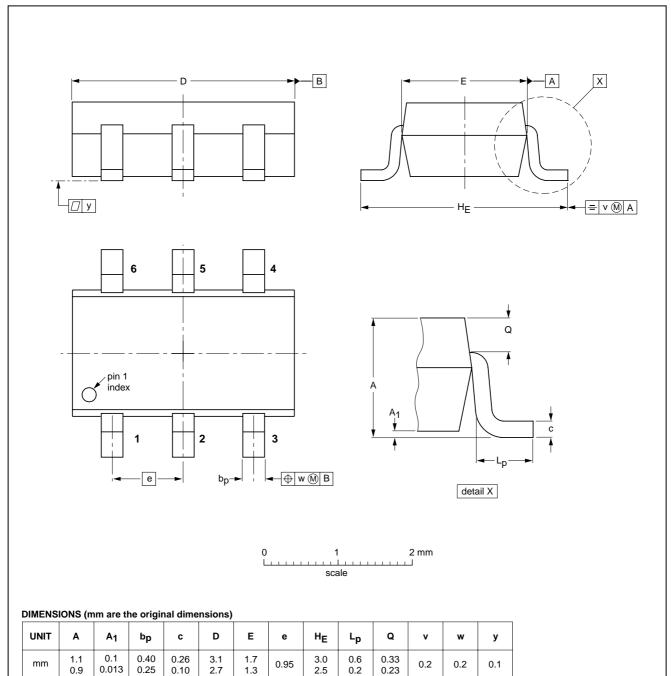
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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

**SOT457** 



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT457			SC-74			<del>-97-02-28-</del> 01-05-04

### NPN general purpose double transistor

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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